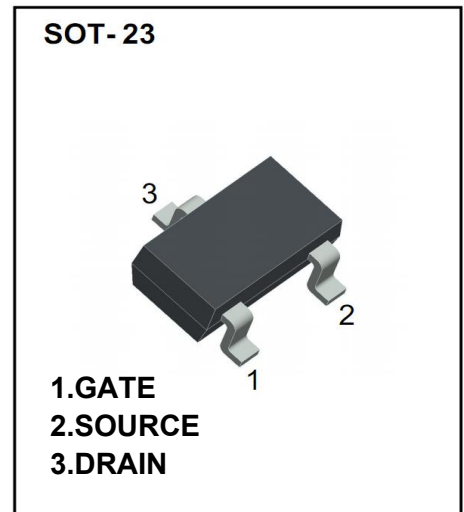
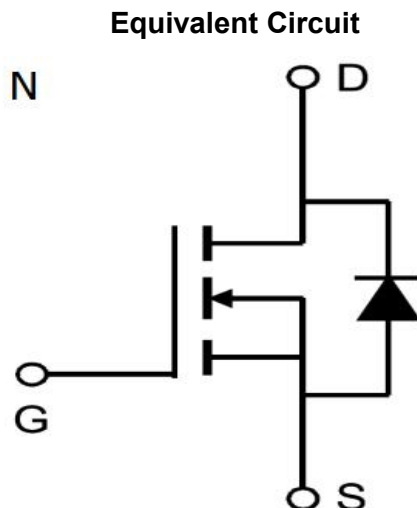
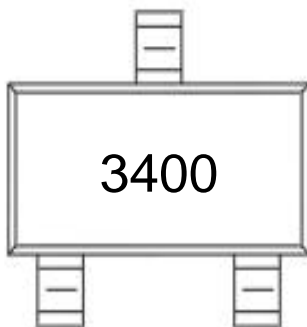


**SOT-23 Plastic-Encapsulate MOSFETS**  
N-Channel Enhancement Mode Field Effect Transistor

**FEATURE**

- High dense cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

**MARKING**



**Maximum ratings (  $T_a=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	5.8	A
Drain Current-Pulsed (note 1)	$I_{DM}$	30	A
Power Dissipation	$P_D$	350	mW
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^{\circ}\text{C}$

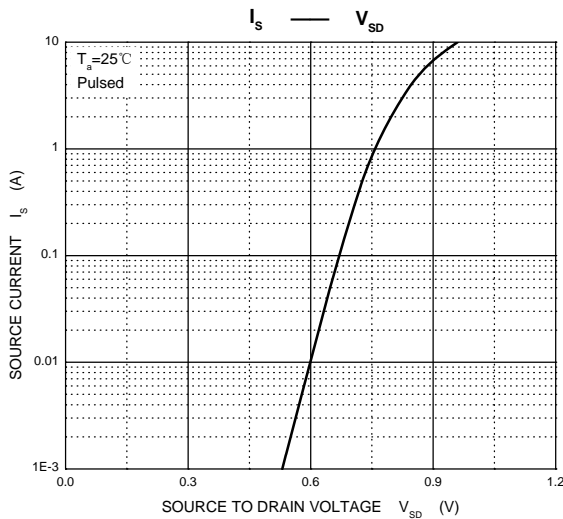
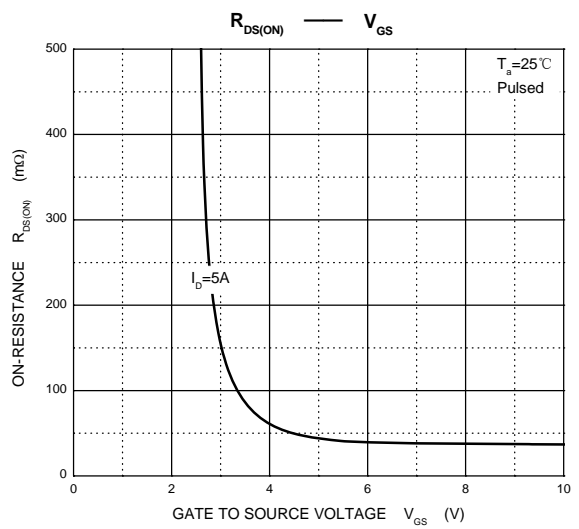
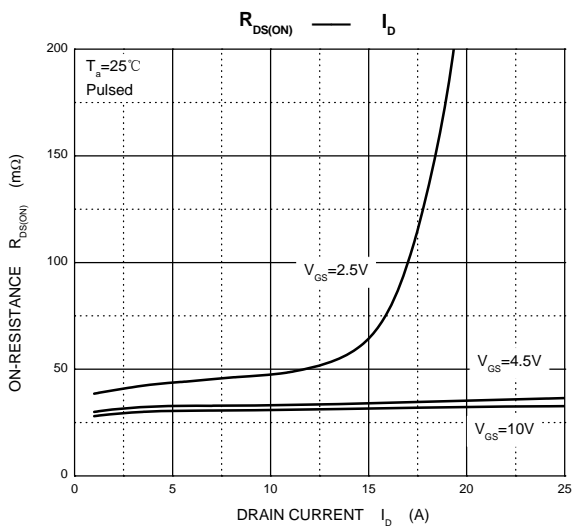
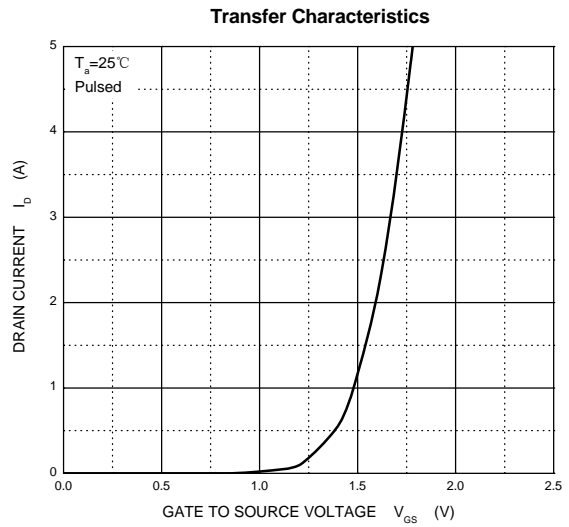
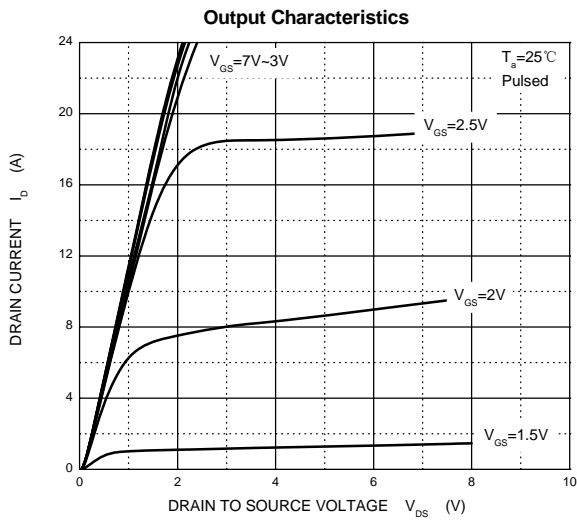
**Electrical characteristics (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V			1	μA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V			±100	nA
<b>On characteristics</b>						
Drain-source on-resistance (note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.8A			35	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A			40	mΩ
Forward tranconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 5A	8			S
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.7		1.4	V
<b>Dynamic Characteristics (note 4,5)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz			1050	pF
Output capacitance	C <sub>oss</sub>			99		pF
Reverse transfer capacitance	C <sub>rss</sub>			77		pF
Gate resistance	R <sub>g</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz			3.6	Ω
<b>Switching Characteristics (note 4,5)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>L</sub> = 2.7Ω, R <sub>GEN</sub> = 3Ω			5	ns
Turn-on rise time	t <sub>r</sub>				7	ns
Turn-off delay time	t <sub>d(off)</sub>				40	ns
Turn-off fall time	t <sub>f</sub>				6	ns
<b>Drain-source diode characteristics and maximum ratings</b>						
Diode forward voltage (note 3)	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V			1	V

**Note :**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

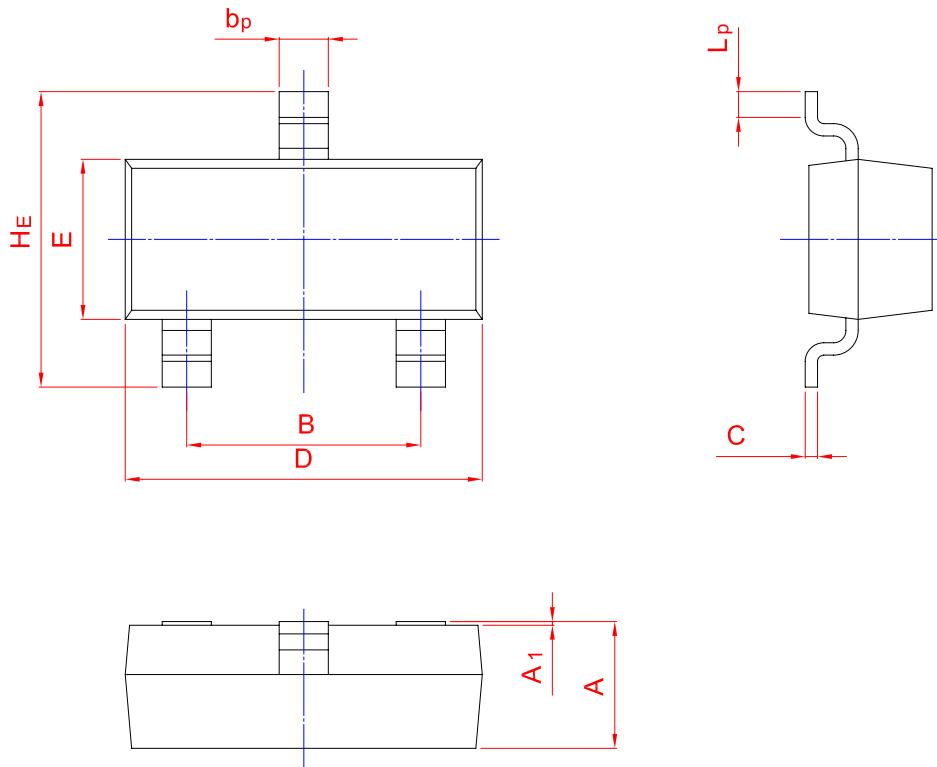
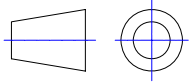
Typical Characteristics



**PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	$b_p$	C	D	E	$H_E$	$A_1$	$L_p$
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

单击下面可查看定价，库存，交付和生命周期等信息

[>>TWGMC\(台湾迪嘉\)](#)